AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. – 2. (Canceled)

3. (Original) A method for manufacturing a semiconductor device, comprising the steps of:

forming a first film pattern by discharging a conductive material with a droplet discharge method;

forming a first photosensitive material over the first film pattern;

forming a first mask pattern by irradiating a region where the first film pattern and the first photosensitive material are overlapped with a laser beam and by developing;

forming a source electrode and a drain electrode having a desired shape by etching the first film pattern using the first mask pattern as a mask;

forming a semiconductor film over the source electrode and the drain electrode;

forming a second photosensitive material over the semiconductor film;

forming a second mask pattern by irradiating the second photosensitive material with a laser beam and by developing;

forming a semiconductor region having a desired shape by etching the semiconductor film using the second mask pattern as a mask; and

forming an insulating film and a gate electrode over the semiconductor region.

4. (Currently Amended) A method for manufacturing a semiconductor device, according to ~~any one of claims 1 to 3~~ claim 3, wherein the first photosensitive material and the second photosensitive material are negative photosensitive resins.

5. (Currently Amended) A method for manufacturing a semiconductor device, according to ~~any one of claims 1 to 3~~ claim 3, wherein the first photosensitive material and the second photosensitive material are positive photosensitive resins.

6. (Currently Amended) A method for manufacturing a semiconductor device, according to ~~any one of claims 1 to 3~~ claim 3, wherein one of the first photosensitive material and the

second photosensitive material is a negative photosensitive resin and the other is a positive photosensitive resin.

7. – 8. (Canceled)

9. (Original) A method for manufacturing a television set, comprising the steps of:

forming a first film pattern by discharging a conductive material with a droplet discharge method;

forming a first photosensitive material over the first film pattern;

forming a first mask pattern by irradiating a region where the first film pattern and the first photosensitive material are overlapped with a laser beam and by developing;

forming a source electrode and a drain electrode having a desired shape by etching the first film pattern using the first mask pattern as a mask;

forming a semiconductor film over the source electrode and the drain electrode;

forming a second photosensitive material over the semiconductor film;

forming a second mask pattern by irradiating the second photosensitive material with a laser beam and by developing;

forming a semiconductor region having a desired shape by etching the semiconductor film using the second mask pattern as a mask;

forming an insulating film and a gate electrode over the semiconductor region; and

forming a pixel electrode to be connected to the drain electrode.

10. (Currently Amended) A method for manufacturing a television set, according to ~~any one of claims 7 to 9~~ claim 9, wherein the first photosensitive material and the second photosensitive material are negative photosensitive resins.

11. (Currently Amended) A method for manufacturing a television set, according to ~~any one of claims 7 to 9~~ claim 9, wherein the first photosensitive material and the second photosensitive material are positive photosensitive resins.

12. (Currently Amended) A method for manufacturing a television set, according to ~~any one of claims 7 to 9~~ claim 9, wherein one of the first photosensitive material and the second

photosensitive material is a negative photosensitive resin and the other is a positive photosensitive resin.

13. (Currently Amended) A method for manufacturing a semiconductor device, according to ~~any one of claims 7 to 9~~ claim 9, wherein the laser beam has any wavelength of from ultraviolet light to infrared light.

14. (Currently Amended) A method for manufacturing a television set, according to ~~any one of claims 7 to 9~~ claim 9, wherein the television set is a liquid crystal television or an EL television.

15. (Currently Amended) A method for manufacturing a semiconductor device, comprising the steps of:

forming a first film pattern over a substrate by a droplet discharge method;

forming a photosensitive material over the first film pattern;

forming a mask pattern by irradiating a region where the first film pattern and the photosensitive material are overlapped with a laser beam while changing a relative position between the substrate and the laser beam and by developing; and

forming a second film pattern having a desired shape by etching the first film pattern using the mask pattern as a mask.

16. (Previously Presented) A method for manufacturing a semiconductor device according to claim 15, further comprising the step of:

forming a third film pattern to be connected to the second film pattern by a droplet discharge method.

17. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the photosensitive material is a negative photosensitive resin.

18. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the photosensitive material is a positive photosensitive resin.

19. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the first film pattern is a conductive film.

20. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the second film pattern is at least one of a gate electrode, a source electrode, or a drain electrode.

21. (Original) A method for manufacturing a semiconductor device according to claim 16, wherein the third film pattern is a wiring.

22. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the first film pattern is a semiconductor film.

23. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the second film pattern has a channel formation region, source region, or a drain region.

24. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the first film pattern is an insulating film.

25. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the second film pattern is an insulating film having an opening.

26. (Currently Amended) A method for manufacturing a semiconductor device, according to ~~any one of claims 1, 2, 3, and 15~~ claim 3, wherein the laser beam has any wavelength of from ultraviolet light to infrared light.

27. – 31. (Canceled)

32. (New) A method for manufacturing a semiconductor device according to claim 15, wherein the laser beam has any wavelength of from ultraviolet light to infrared light.